



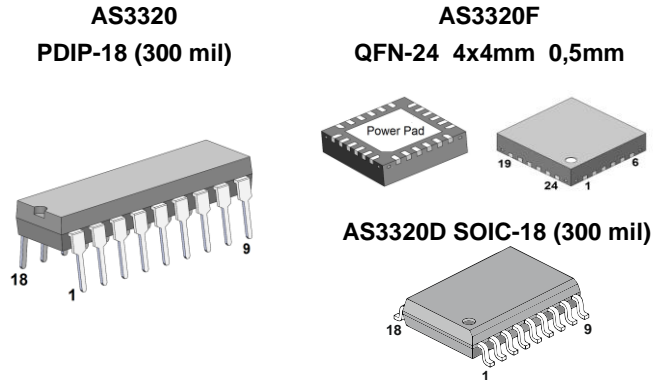
AS3320 - Voltage controlled filter (VCF)

FEATURES

- voltage controllable frequency - 12 octave range
- voltage controllable resonance - from zero to oscillation
- accurate exponential frequency scale
- accurate linear resonance scale
- low control voltage feedthrough -45dB typical
- filter configurable into LPF, HPF, all pass, etc.
- low noise: -86dB typical
- low distortion in passband - 0.1% typical
- low warm up drift
- configurable into low distortion voltage controlled sine wave oscillator
- bandwidth till 800kHz

APPLICATIONS

for electronic music



General Description

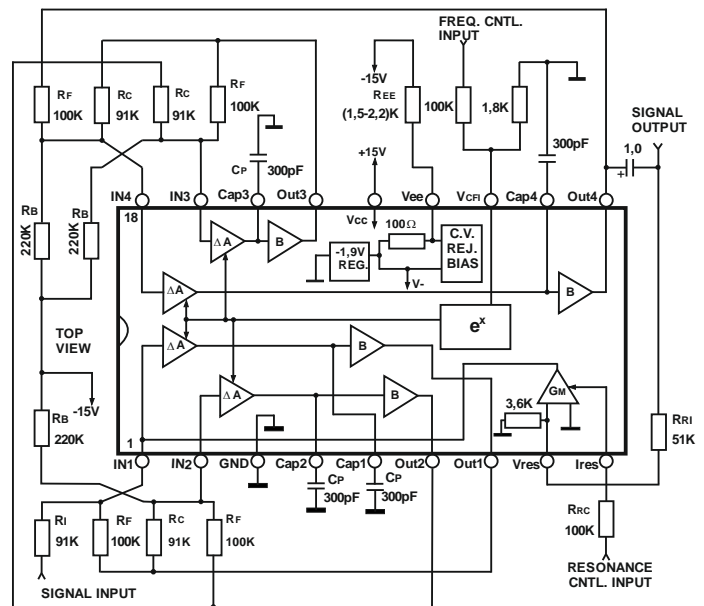
The AS3320 is a high performance voltage controlled four-pole filter with on-chip voltage controllable resonance IC. The four independent sections may be interconnected to provide a wide variety of filter responses, such as low pass, high pass, band pass and all pass. A single input exponentially controls the frequency over greater than a ten octave range with little control voltage feedthrough. Another input controls the resonance in a modified linear manner from zero to low distortion oscillation. For those demanding applications, provision has been made to allow trimming for improved control voltage rejection. Each filter section features a variable gain cell which is fully temperature compensated, exhibits a better signal-to-noise ratio and generates its low distortion predominantly in the second harmonic. The device includes a minus two volt regulator to ensure low power dissipation and consequent low warm-up drift.

Power pad in QFN package highly improves thermal stability of parameters of AS3320F.

Pin Information

PDIP-18, SOICW-18 Pin No	QFN-24L Pin No	Pin Name	Description
1	4	IN1	Input Stage 1
2	5	IN2	Input Stage 2
3	7	GND	Ground
4	8	Cap2	Capacitor Stage 2
5	9	Cap1	Capacitor Stage 1
6	11	Out2	Output Stage 2
7	12	Out1	Output Stage 1
8	14	Vres	Resonance Input
9	15	Ires	Resonance Control Input
10	16	Out4	Output Stage 4
11	17	Cap4	Capacitor Stage 4
12	19	V _{CFI}	Voltage Control Frequency Input
13	20	Vee	Negative power
14	22	Vcc	Positive power
15	23	Out3	Output Stage 3
16	24	Cap3	Capacitor Stage 3
17	2	IN3	Input Stage 3
18	3	IN4	Input Stage 4
-	Power pad	Power pad	Don't connect

Circuit Block and Connection Diagram (PDIP-18, SOIC-18)



Absolute Maximum Ratings

Voltage between Vcc and Vee pins	+22V, -0,5V
Voltage between Vcc and GND pins	+18V, -0,5V
Voltage between Vee and GND pins	-4V, -0,5V
Voltage between Cell Input and GND pins	+0,5V, -6V
Voltage between Frequency Control and GND pins	±6V
Voltage between Resonance Control and GND pins	+2V, -18V
Current through any pin	±40mA
Storage Temperature Range	- 55°C to 150°C
Operating Temperature Range	- 25°C to 75°C



Electrical Characteristics *

$V_{CC}=+15V$ $R_F = 100K$ $T_A= 25^{\circ}C$

Parameter	Min.	Typ.	Max.	Units
Gain of Variable Gain Cell at $V_{CFI}=0$	0.7	1	1,3	
Input Bias Current of Frequency Control Input	0.2	1	1.5	μA
Input Impedance of Resonance Signal Input	2.7	3.6	4.5	$K \Omega$
Output Swing At Clipping	10	12	14	V.P.P.
Output voltage DC ¹	5	6.5	9	V
Buffer Input Bias Current	± 10	± 30	± 100	nA
Buffer Output Impedance ²	25	50	100	Ω
Voltage at the negative supply pin ³	-2.4	-2.7	-2.9	V
Positive Supply Current, I_{CC}	3.8	5	6.5	mA
Negative Supply Current, I_{EE} ³	8	8.4	8.8	mA

Typical Electrical Characteristics

Parameter	Min.	Typ.	Max.	Units
Pole Frequency Control Range ⁴	3500:1	10,000:1	-	
Sensitivity of Pole Frequency Control Scale, Midrange	57.5	60	62.5	mV/decade
Tempco of Pole Frequency Control Scale	3000	3300	3600	ppm
Exponential Error of Pole Frequency Control Scale ⁵	-	4	12	%
Max Gain of Variable Gain Cell	2.4	3	3.6	
Tempco of Variable Gain Cell ⁶	-	500	1500	ppm
Output Impedance of Gain Cell ⁶	0.5	1	2	$M \Omega$
Pole Frequency Control Feedthrough	-	60	200	mV
Pole Frequency Warm-up Drift	-	0.5	1.5	%
Gm of Resonance Control Element at $I_{CR}=100\mu A$	0.8	1	1.2	mmhos
Amount of Resonance Obtainable Before Oscillation	20	30	-	dB
Resonance Control Feedthrough ⁷	-	0.2	1,5	V
Output Noise re Max Output ⁸	-76	-86	-	dB
Rejection in Bandreject	73	83	-	dB
Distortion in Passband ^{9,11}	-	0.1	0.3	%
Distortion in Bandreject ^{10,11}	-	0.3	1	%
Distortion of Sine Wave Oscillation ¹²	-	0.5	1.5	%
Internal Reference Current, I_{REF}	45	63	85	μA
Buffer Slew Rate	1.5	3	-	$V/\mu S$
Buffer Sink Capability	0.4	0.5	0.63	mA
Positive Supply Range, V_{CC}	+9	-	+18	V
Negative Supply Range, V_{EE} ³	-4	-	-18	V

***) Specifications subject to change without notice.**

Note 1: $V_{IN} = 0$, $R_C = 91K\Omega$, $R_F = 100K\Omega$

Note 2: $V_{CFI} = 0$

Note 3: Current limiting resistor always required. $R_{EE} = (15V - 2.7V) / 8.4 \text{ mA} \sim 1.5k$
for negative supply -15V

Note 4: $-20mV < V_{CFI} < +160mV$

Note 5: $-16mV < V_{CFI} < +176mV$. Most of this error occurs in upper two octaves.

Note 6: $V_{CFI} = 0$

Note 7: Untrimmed. $0 < I_{CR} < 100\mu A$

Note 8: Filter is connected as low pass and set for 20 KHz cut-off frequency.

Note 9: Output signal is 3dB below clipping point.

Note 10: Output signal is 3dB below passband level, which is 3dB below clipping point. In general, this is worst case condition.

Note 11: Distortion is predominantly second harmonic.

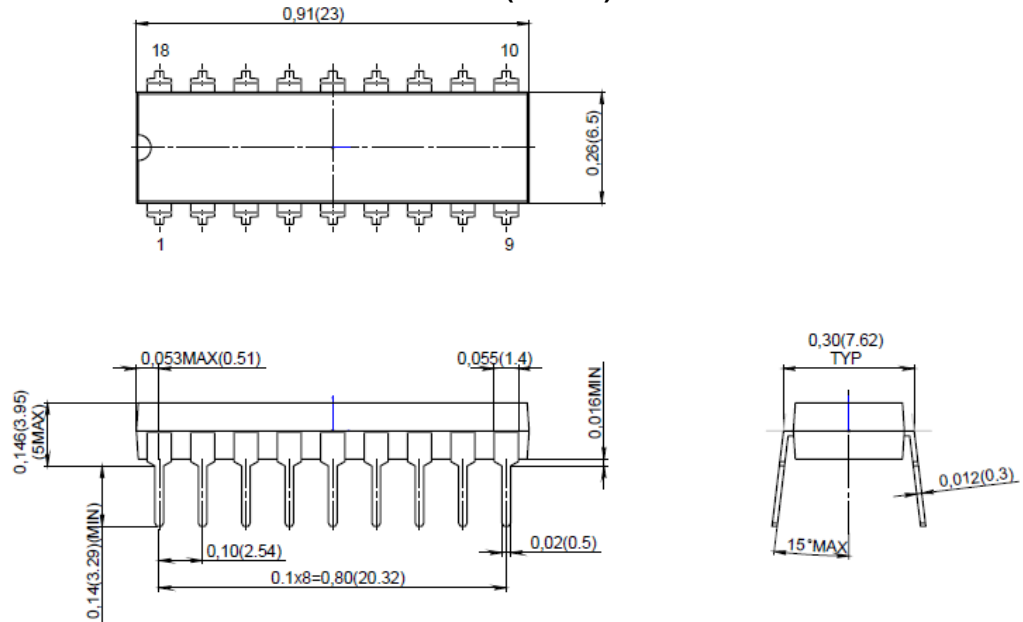
Note 12: Sinewave is not clipped by first stage.



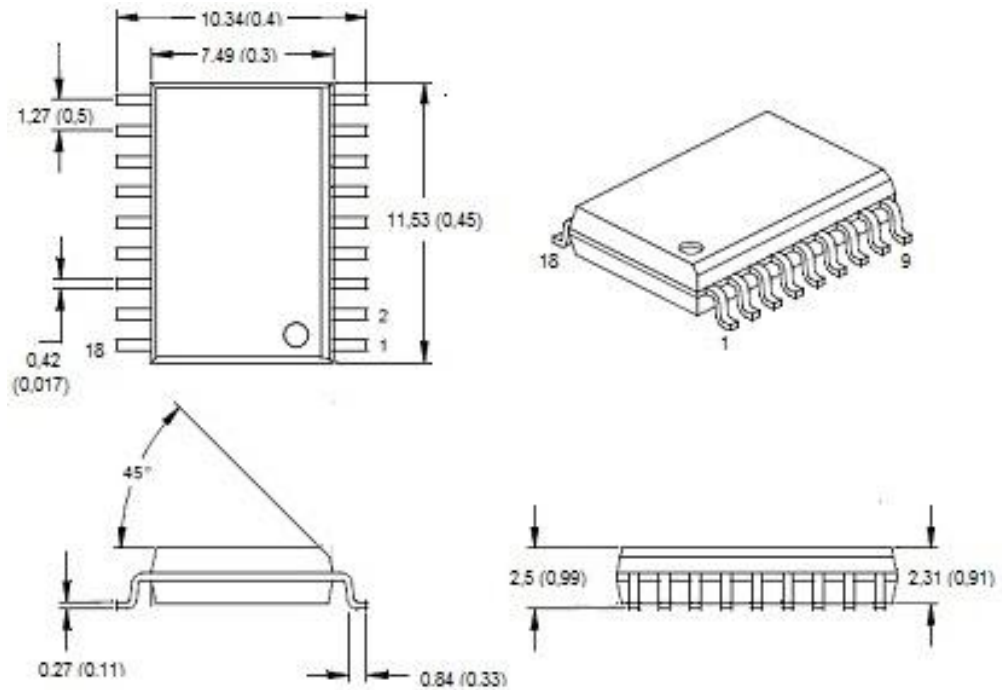
Device type	Package
AS3320	PDIP-18 (300 mil body)
AS3320D	SOIC-18 (300 mil body)
AS3320F	QFN-24L (4*4 mm 0.5 mm)

Package Information

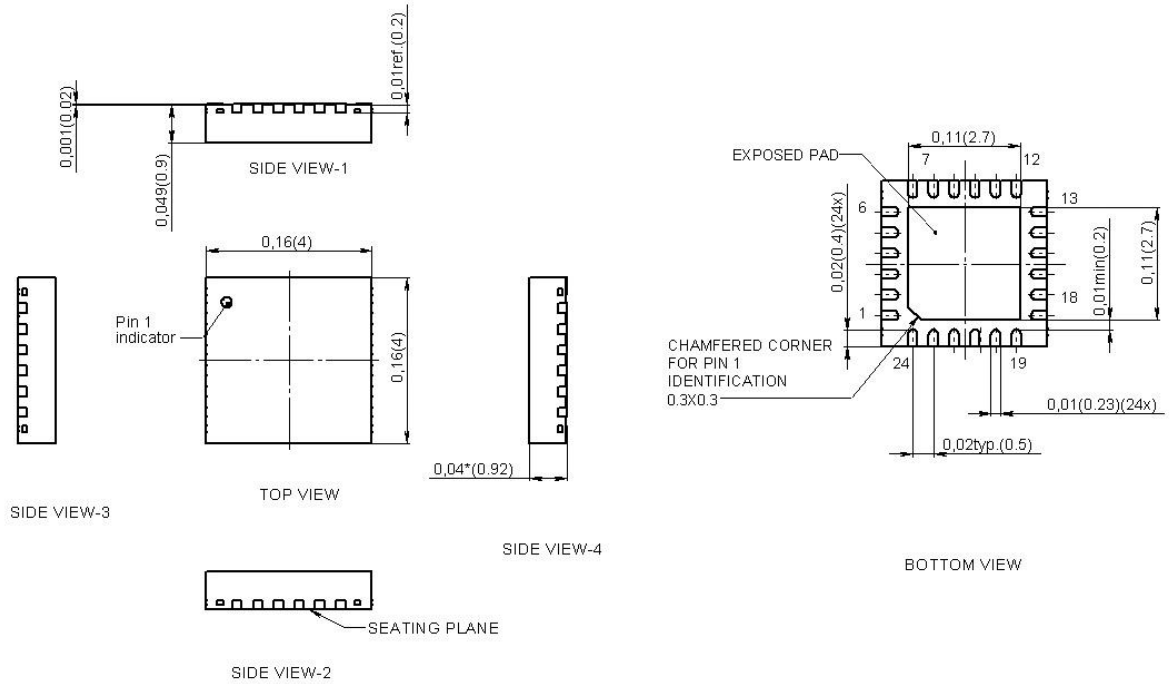
PDIP-18 (300 mil)



SOIC-18 (300 mil)



QFN-24 4x4 mm 0.5 mm



Revision history

Date	Revision	Changes
05-Oct-2016	1	Short version 1
09-Jan-2017	2	QFN-24L – new package
20-Mar-2017	3	Drawing and typical electrical characteristics updated
09-May-2017	4	Block circuit and typical electrical characteristics updated
29-May-2017	5	Minor changes
21-May-2018	6	Minor changes
10-Jun-2019	7	SOICW-18L – new package
27-May-2020	8	Note 3 correction